

# Michael A Oakley

## List of Publications by Year in descending order

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16  
papers

142  
citations

1307594

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1372567

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all docs

16  
docs citations

16  
times ranked

144  
citing authors

#	ARTICLE	IF	CITATIONS
1	Limiting Effects on the Design of Vertical Superjunction Collectors in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 793-797.	3.0	0
2	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	2.0	9
3	A 0.3-15 GHz SiGe LNA With >1 THz Gain-Bandwidth Product. IEEE Microwave and Wireless Components Letters, 2017, 27, 380-382.	3.2	11
4	Predicting hard failures and maximum usable range of siGe HBTs. , 2017, , .		1
5	SiGe Technology as a Millimeter-Wave Platform: Scaling Issues, Reliability Physics, Circuit Performance, and New Opportunities. , 2016, , .		5
6	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	2.0	13
7	Inverse class-F-X-band S/G/e HBT power amplifier with 44% PAE and 24.5 dBm peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
8	On the use of vertical superjunction collectors for enhanced breakdown performance in SiGe HBTs. , 2016, , .		4
9	Optimizing the vertical profile of SiGe HBTs to mitigate radiation-induced upsets. , 2015, , .		5
10	Single-Event Effects in a W-Band (75-110 GHz) Radar Down-Conversion Mixer Implemented in 90 nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	2.0	12
11	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	2.0	4
12	On the Cryogenic RF Linearity of SiGe HBTs in a Fourth-Generation 90-nm SiGe BiCMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 1127-1135.	3.0	5
13	Large-Signal Reliability Analysis of SiGe HBT Cascode Driver Amplifiers. IEEE Transactions on Electron Devices, 2015, 62, 1383-1389.	3.0	28
14	A Class-E Tuned W-Band SiGe Power Amplifier With 40.4% Power-Added Efficiency at 93 GHz. IEEE Microwave and Wireless Components Letters, 2015, 25, 663-665.	3.2	26
15	An Investigation of Single-Event Transients in C-SiGe HBT on SOI Current Mirror Circuits. IEEE Transactions on Nuclear Science, 2014, 61, 3193-3200.	2.0	15
16	On the reliability of SiGe HBT cascode driver amplifiers. , 2014, , .		3